Product data sheet

1. Product profile

1.1 General description

Single planar Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a very small and flat lead SOD323F (SC-90) Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Low forward voltage
- Reverse voltage V_R ≤ 100 V
- Very small and flat lead SMD plastic package
- Low capacitance
- AEC-Q101 qualified

1.3 Applications

- High-speed switching
- Line termination

- Voltage clamping
- Reverse polarity protection

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{R}	reverse voltage		-	-	100	V
V _F	forward voltage	$I_F = 250 \text{ mA}$	<u>[1]</u> _	-	850	mV
I _R	reverse current	$V_R = 75 V$	<u>[1]</u> _	-	4	μΑ

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	. [4]
2	anode		1 2
			sym001

^[1] The marking bar indicates the cathode.



Single Schottky barrier diode

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BAT46WJ	SC-90	plastic surface-mounted package; 2 leads	SOD323F

4. Marking

Table 4. Marking codes

Type number	Marking code
BAT46WJ	JK

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage		-	100	V
I _F	forward current		-	250	mA
I _{FSM}	non-repetitive peak forward current	square wave; t _p < 10 ms	[1] -	2.5	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[2][4]	400	mW
			[3][4]	715	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T_{stg}	storage temperature		-65	+150	°C

^[1] $T_j = 25$ °C before surge.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1][3]	-	-	310	K/W
junction to ambient	junction to ambient		[2][3]	-	-	175	K/W

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

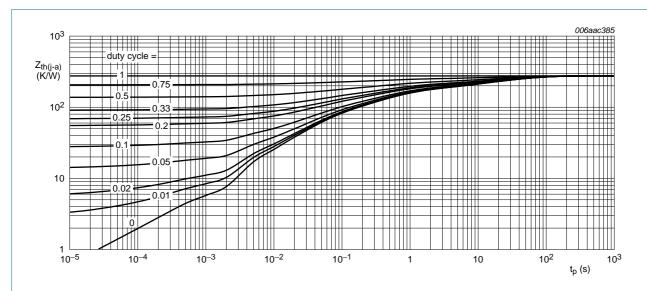
^[4] Reflow soldering is the only recommended soldering method.

Single Schottky barrier diode

Table 6. Thermal characteristics ...continued

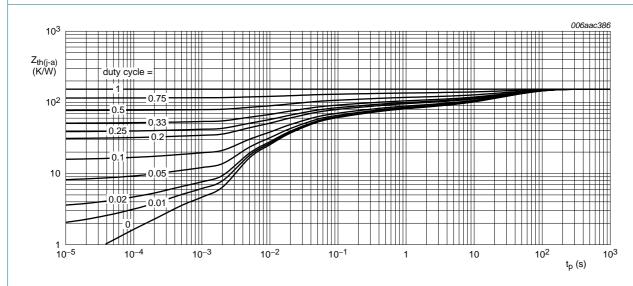
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[4]</u> _	-	35	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [3] Reflow soldering is the only recommended soldering method.
- [4] Soldering point of cathode tab.



FR4 PCB, standard footprint

Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm²

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

Single Schottky barrier diode

7. Characteristics

Table 7. Characteristics

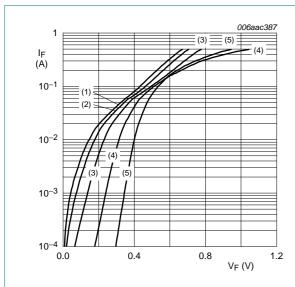
 $T_{amb} = 25$ °C unless otherwise specified.

· arrib — 20	o Camess surerwise specimea.					
Symbol	Parameter	Conditions	Mir	า Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
		$I_F = 0.1 \text{ mA}$	-	175	200	mV
	$I_F = 10 \text{ mA}$	-	315	350	mV	
	$I_F = 10 \text{ mA}; T_j = -40 ^{\circ}\text{C}$	-	-	470	mV	
	$I_F = 50 \text{ mA}$	-	415	475	mV	
	$I_F = 50 \text{ mA}; T_j = -40 ^{\circ}\text{C}$	-	-	560	mV	
		$I_F = 250 \text{ mA}$	-	710	850	mV
I _R	reverse current		[1]			
		V _R = 1.5 V	-	0.2	0.5	μΑ
		$V_R = 1.5 \text{ V}; T_j = 60 ^{\circ}\text{C}$	-	-	12	μΑ
		V _R = 10 V	-	0.3	8.0	μΑ
		$V_R = 10 \text{ V}; T_j = 60 ^{\circ}\text{C}$	-	-	20	μΑ
		V _R = 50 V	-	0.7	2	μΑ
		$V_R = 50 \text{ V}; T_j = 60 ^{\circ}\text{C}$	-	-	44	μΑ
		V _R = 75 V	-	1	4	μΑ
		$V_R = 75 \text{ V}; T_j = 60 ^{\circ}\text{C}$	-	-	80	μΑ
		V _R = 100 V	-	2	9	μΑ
		$V_R = 100 \text{ V}; T_j = 60 ^{\circ}\text{C}$	-	-	120	μΑ
		$V_R = 100 \text{ V}; T_j = 85 ^{\circ}\text{C}$	-	-	600	μΑ
C _d	diode capacitance	f = 1 MHz				
		$V_R = 0 V$	-	-	39	pF
		V _R = 1 V	-	-	21	pF
t _{rr}	reverse recovery time		[2] -	5.9	-	ns

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

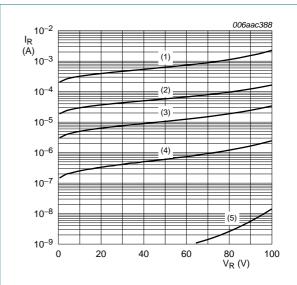
^[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 $\Omega;$ measured at I_R = 1 mA.

Single Schottky barrier diode



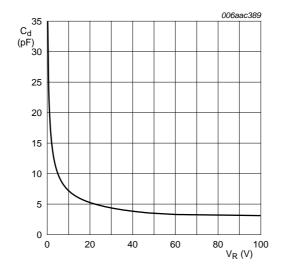
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 3. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 60 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

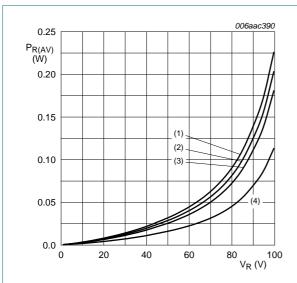
Fig 4. Reverse current as a function of reverse voltage; typical values



f = 1 MHz; T_{amb} = 25 °C

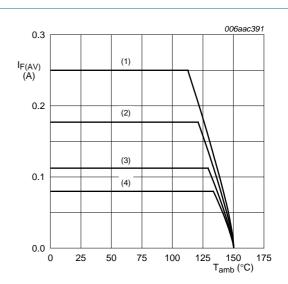
Fig 5. Diode capacitance as a function of reverse voltage; typical values

Single Schottky barrier diode



- (1) $\delta = 1$
- (2) $\delta = 0.9$
- (3) $\delta = 0.8$
- (4) $\delta = 0.5$

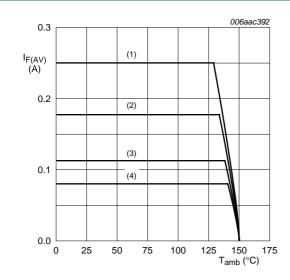
Fig 6. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

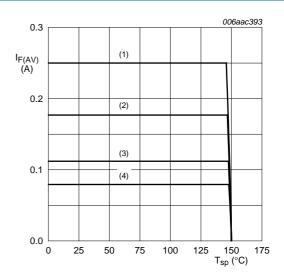
Fig 7. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Fig 8. Average forward current as a function of ambient temperature; typical values



T_i = 150 °C

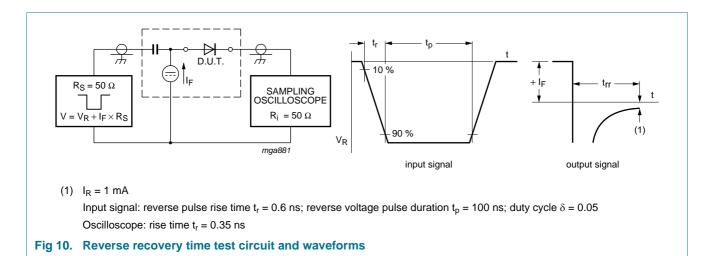
- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

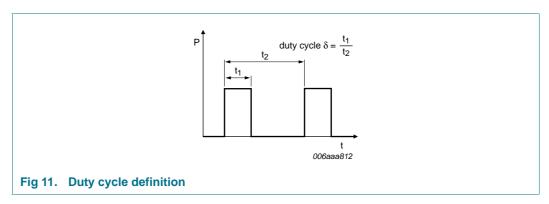
Fig 9. Average forward current as a function of solder point temperature; typical values

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Single Schottky barrier diode

8. Test information





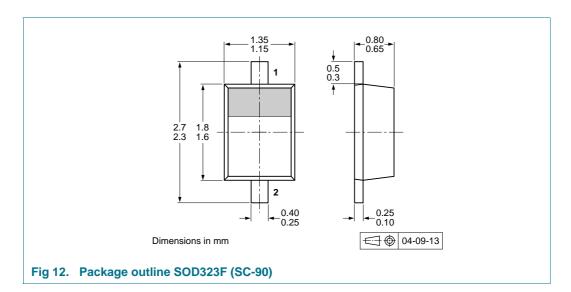
The current ratings for the typical waveforms as shown in Figure 7, 8 and 9 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Single Schottky barrier diode

9. Package outline



10. Packing information

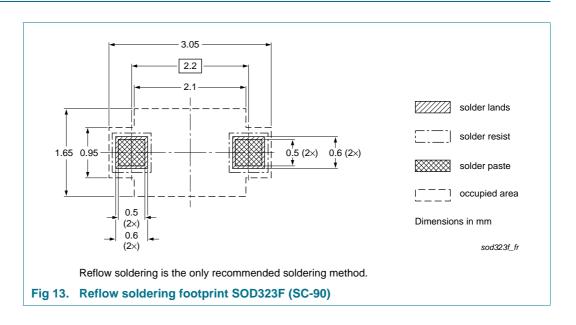
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing q	uantity
			3000	10000
BAT46WJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAT46WJ v.2	20111108	Product data sheet	-	BAT46WJ v.1
Modifications:	 <u>Table 7</u>: unit for reverse current I_R at V_R = 50 V corrected to μA 			
	 <u>Table 7</u>: conditions of reverse voltage V_R corrected 			
	 Section 13 "I 	<u>egal information</u> ": updated		
BAT46WJ v.1	20100728	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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BAT46WJ NXP Semiconductors

Single Schottky barrier diode

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